FIG. 1A

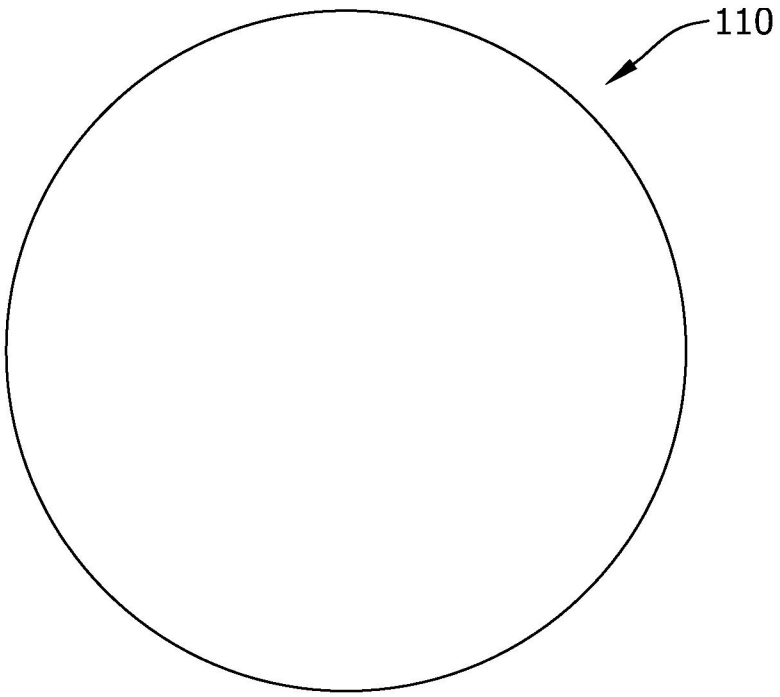


FIG. 1B

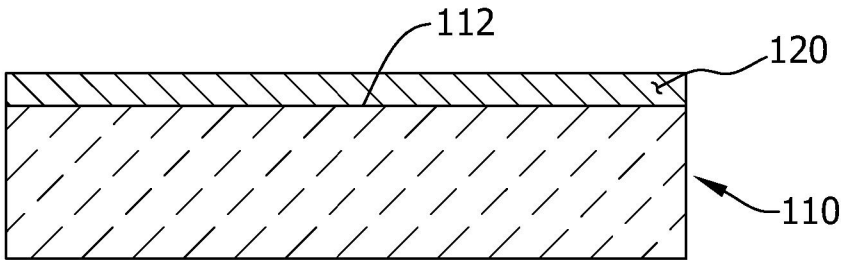


FIG. 2

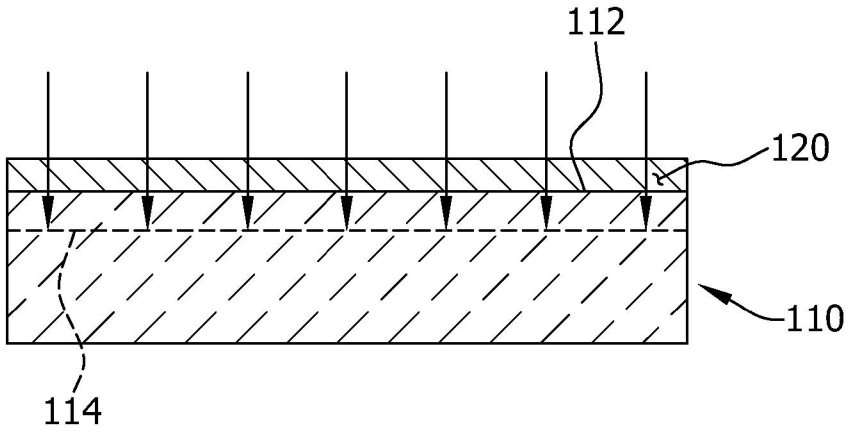


FIG. 3

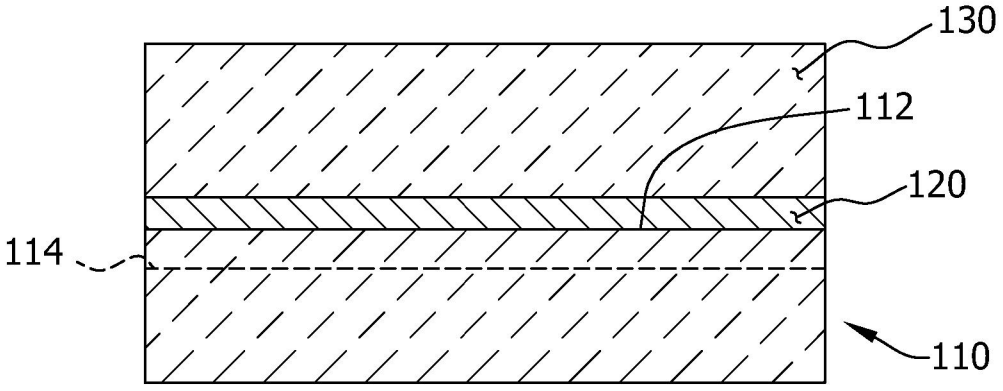


FIG. 4

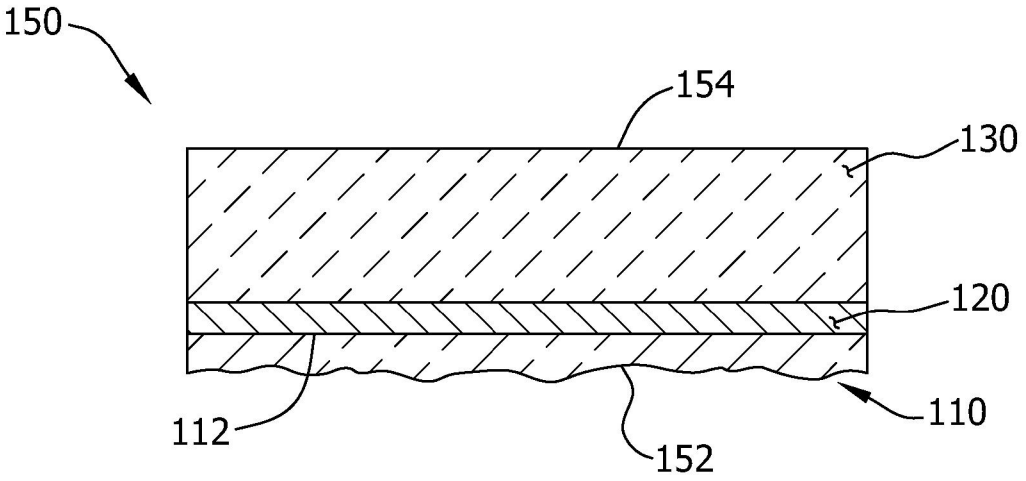


FIG. 5

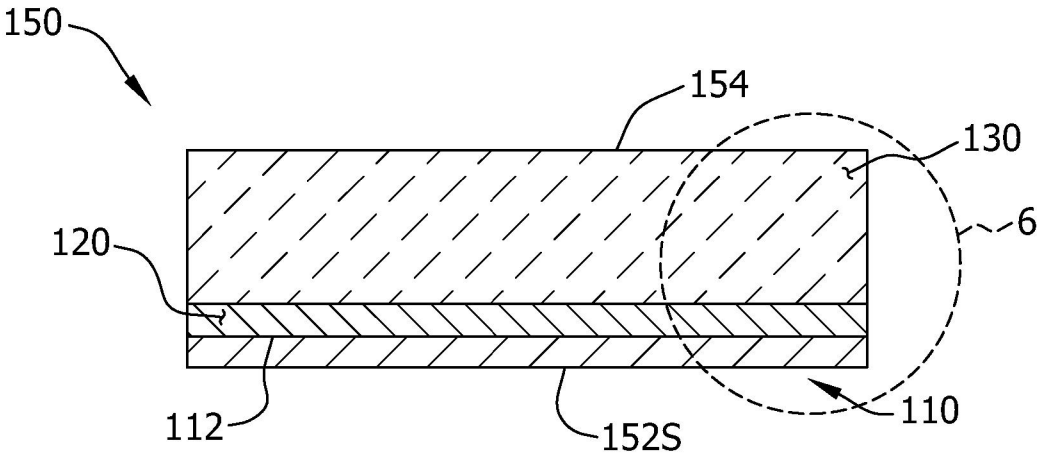


FIG. 6

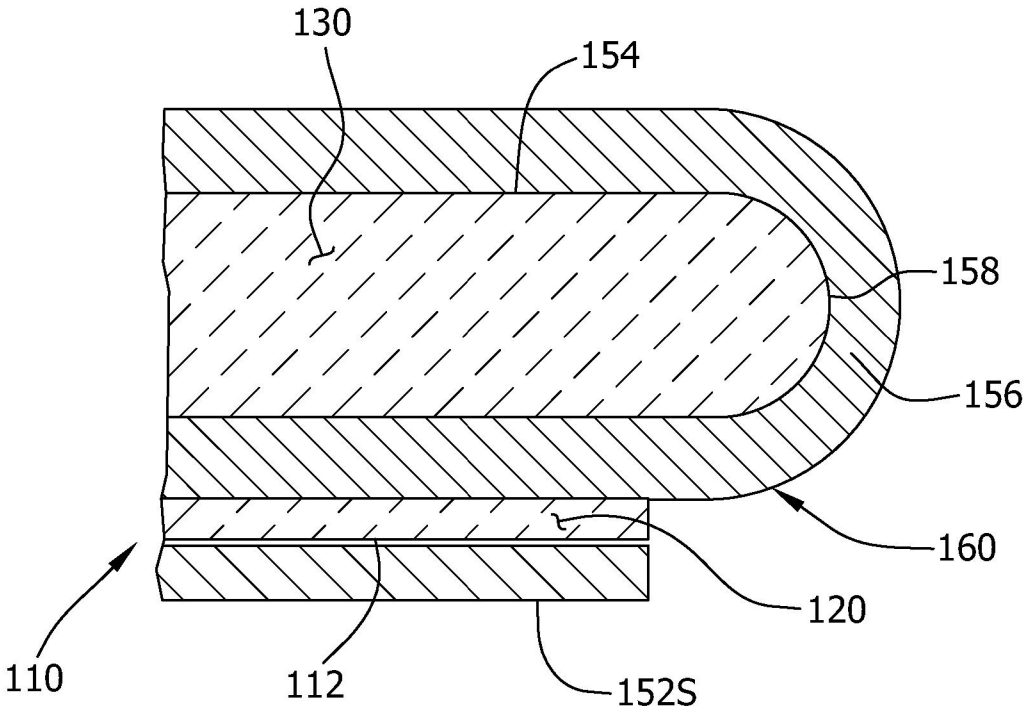


FIG. 7

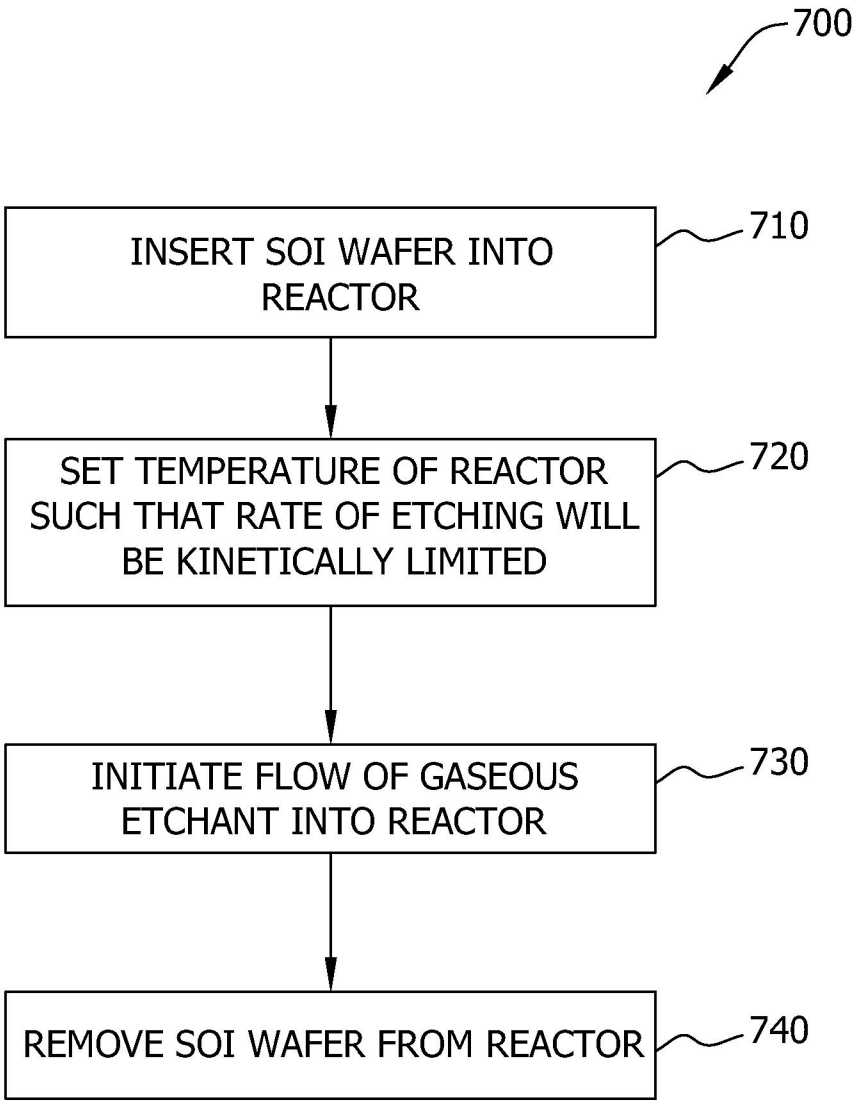

700
INSERT SOI WAFER INTO REACTOR
710
SET TEMPERATURE OF REACTOR SUCH THAT RATE OF ETCHING WILL BE KINETICALLY LIMITED
720
INITIATE FLOW OF GASEOUS ETCHANT INTO REACTOR
730
REMOVE SOI WAFER FROM REACTOR
740

FIG. 8

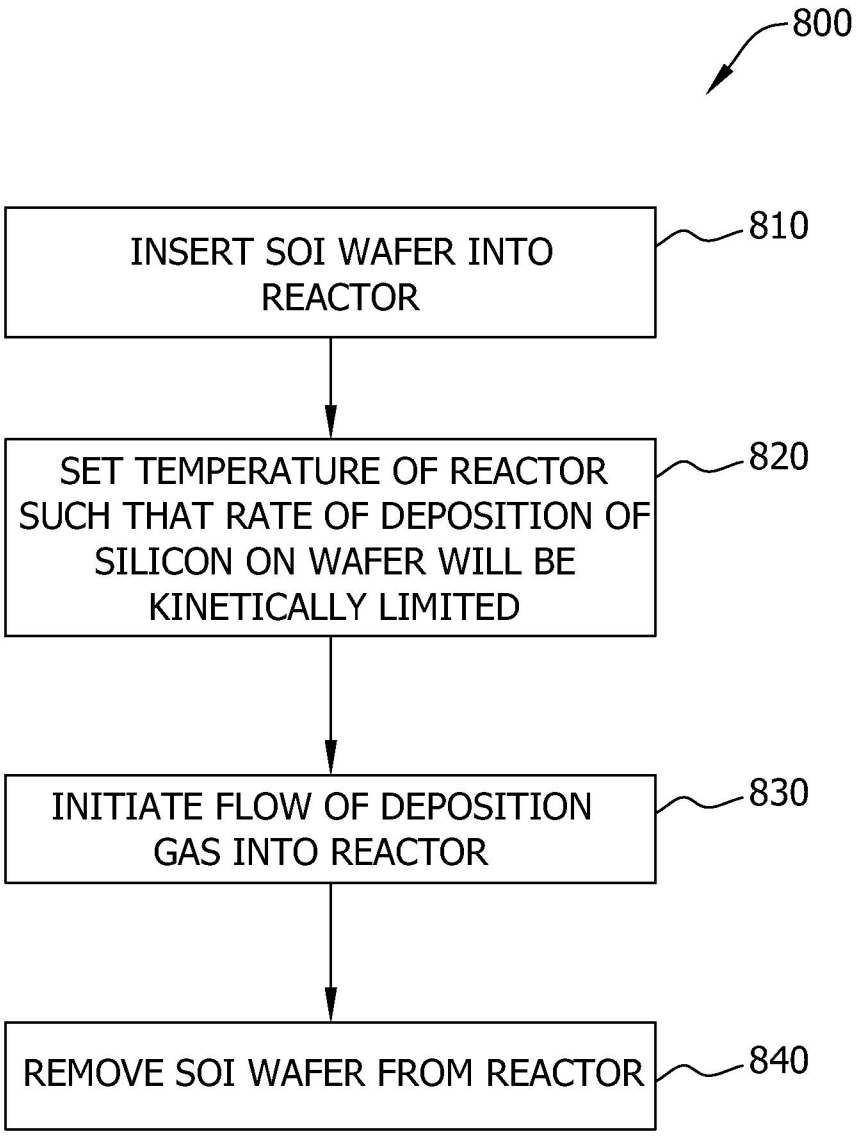

800
INSERT SOI WAFER INTO REACTOR
810
SET TEMPERATURE OF REACTOR SUCH THAT RATE OF DEPOSITION OF SILICON ON WAFER WILL BE KINETICALLY LIMITED
820
INITIATE FLOW OF DEPOSITION GAS INTO REACTOR
830
REMOVE SOI WAFER FROM REACTOR
840

FIG. 9

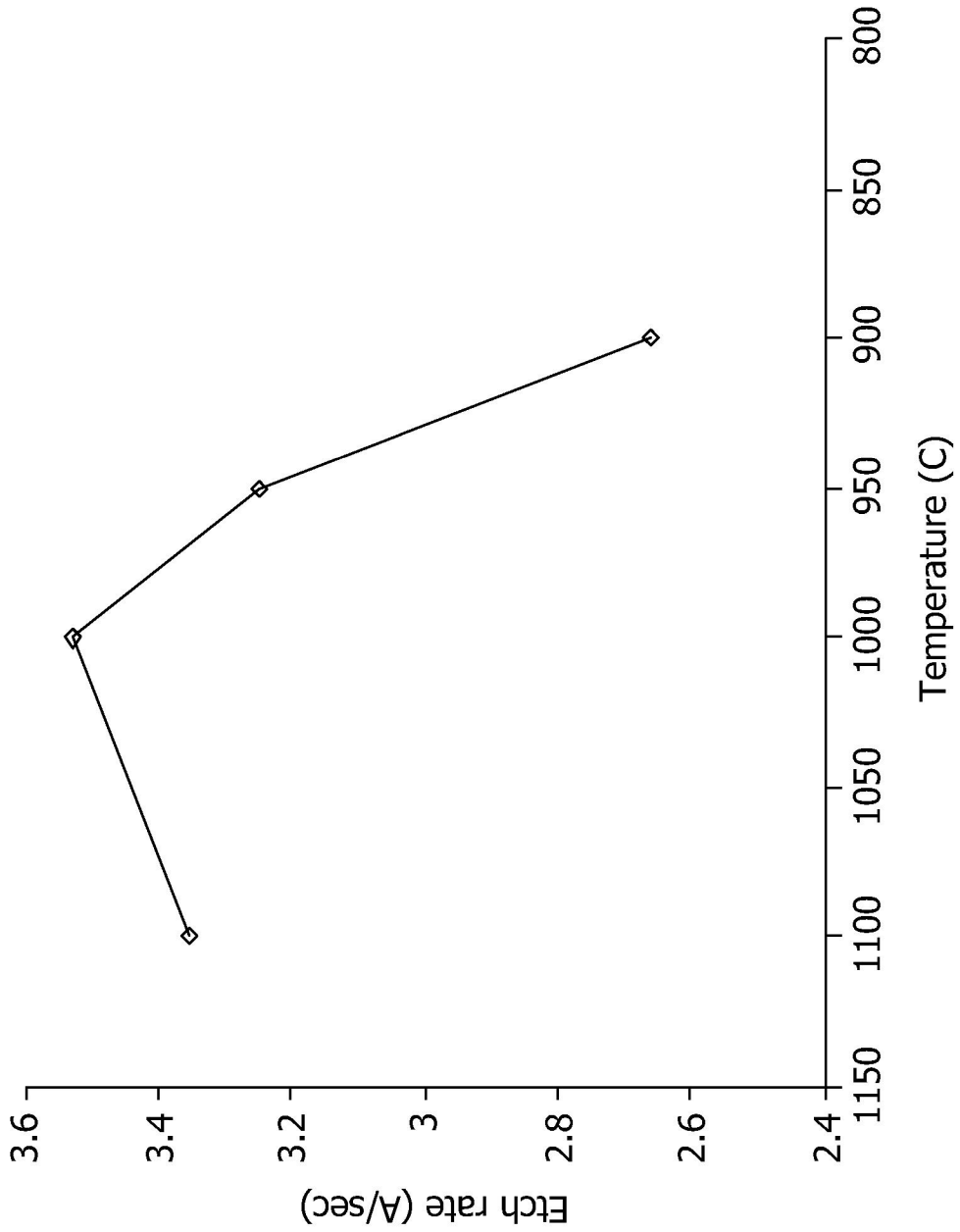

Etch rate (A/sec)
3.6
3.4
3.2
3
2.8
2.6
2.4
1150
1100
1050
1000
950
900
850
800
Temperature (C)

FIG. 10A

FIG. 10B

FIG. 10C

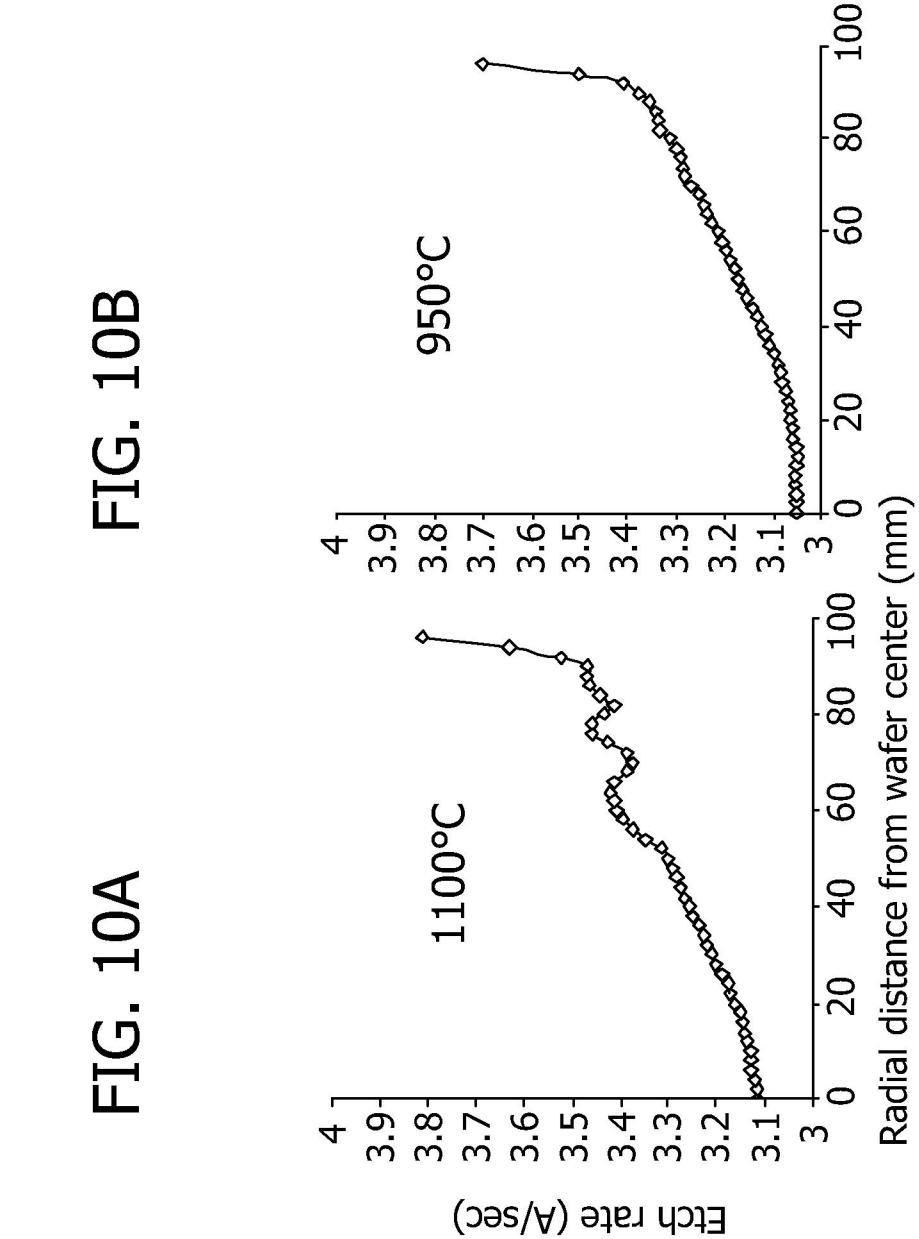
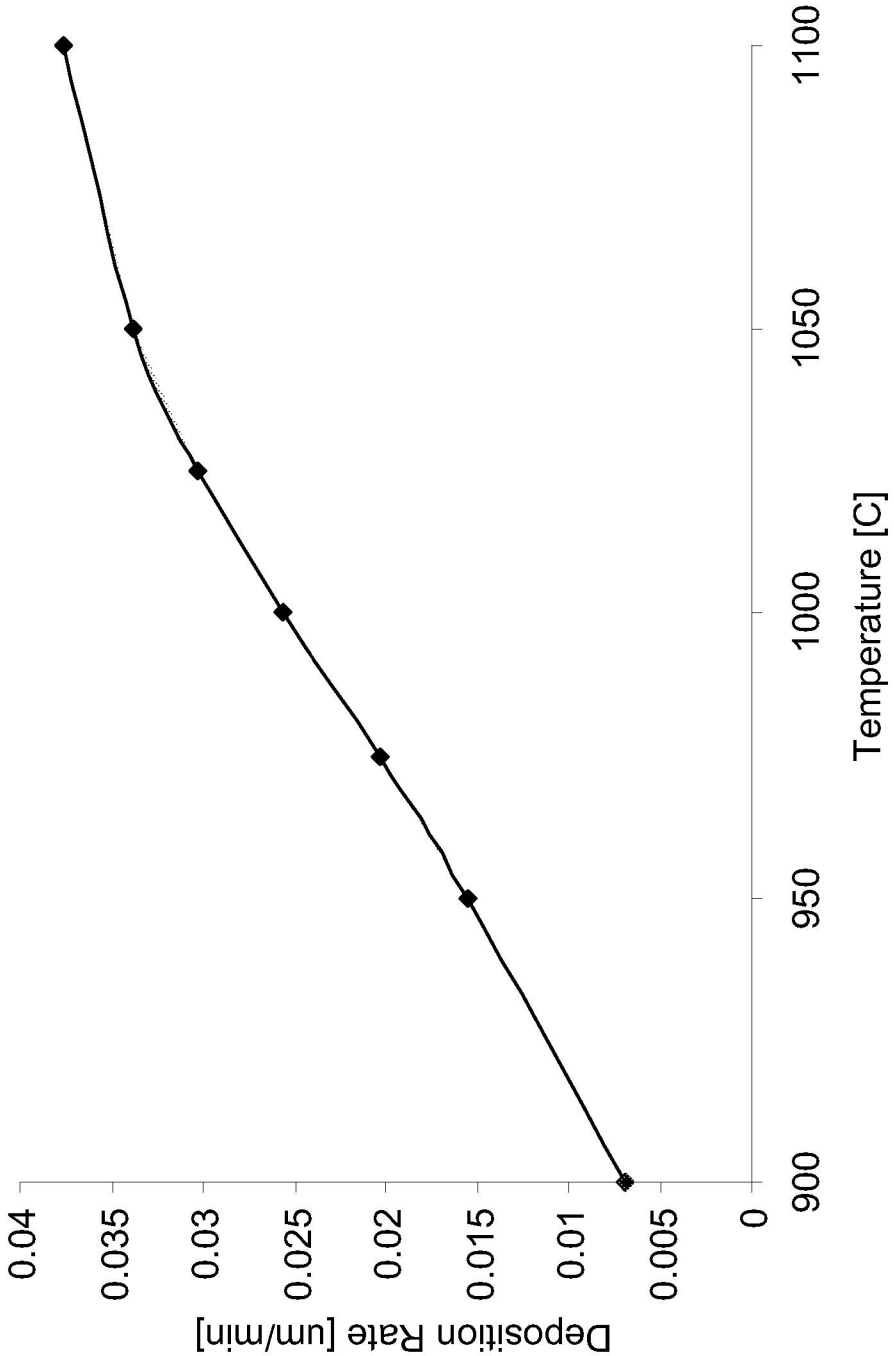


FIG. 11


Deposition Rate [um/min]
0.04
0.035
0.03
0.025
0.02
0.015
0.01
0.005
0
900
950
1000
1050
1100
Temperature [C]